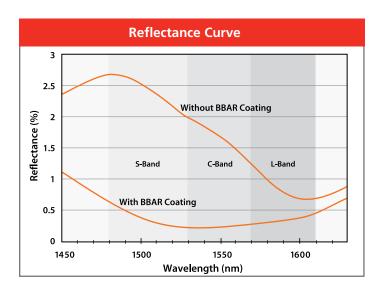
# FCI-InGaAs-WCER-LR

## Broadband Anti-Reflection Coated InGaAs Photodiodes

OSI Optoelectronics's latest product line includes a very low reflectance photodiode. Designed for telecommunication applications, the InGaAs/InP photodiode has a typical optical reflectance of less than .6% from 1520nm to 1620nm. This ultra low reflectance over the wide wavelength range was achieved by depositing a proprietary multi-layered Anti-Reflection coating directly onto the surface of the InGaAs/InP photodiode.



Absolute Maximum Ratings								
PARAMETERS	SYMBOL	MIN	MAX	UNITS				
Storage Temperature	T <sub>stg</sub>	-40	+85	°C				
Operating Temperature	T <sub>op</sub>	0	+70	°C				
Soldering Temperature	T <sub>sld</sub>		+260	°C				

Electro-Optical Characteristics T <sub>A</sub> =23°C								
PARAMETERS	SYMBOL	CONDITIONS	MIN	TYP	мах	UNITS		
Active Area	AA			250X500		μm X μm		
Responsivity		λ = 1310nm	0.85	0.90		A/W		
	R <sub>λ</sub>	λ = 1550nm	0.90	0.95				
Capacitance	C <sub>j</sub>	V <sub>R</sub> =5.0V		15		pF		
Dark Current	I <sub>d</sub>	V <sub>R</sub> =5.0V			1	nA		
Max. Reverse Voltage					20	V		
Max. Reverse Current					2	mA		
Max. Forward Current					5	mA		
Reflectance		1520nm≤ λ ≤1620nm		0.5	0.6	%		

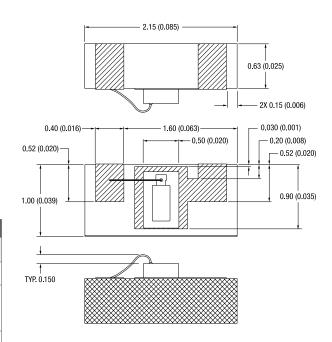


#### **APPLICATIONS**

- Wavelength Locker / Wavelength Monitoring
- Lasers Back Facet Monitoring
- DWDM
- Instrumentation

### **FEATURES**

- Reflectance Less than 0.6%
- Low Noise
- High Responsivity
- High Speed
- Spectral Range 900nm to 1700nm



## Notes:

- All units in millimeters.
- All devices are mounted with low out gassing conductive epoxy with tolerance of ±25µm. Eutectic mounting is also available upon request.



